

View Online at <https://aerobasegroup.com/nsn/5961-01-065-9027>

Inclosure Material:

Ceramic all transistor and metal all transistor

Overall Length:

1.000 inches 4th transistor

Overall Height:

0.300 inches 4th transistor

Overall Width:

1.000 inches 4th transistor

Mounting Facility Quantity:

2 all transistor

Internal Configuration:

Junction contact all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

4 transistor

Mounting Method:

Unthreaded hole all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

35.0 collector to emitter voltage/static/base open 2nd transistor and 60.0 collector to emitter voltage, dc with base short-circuited to emitter 2nd transistor and 4.0 emitter to base voltage, static, collector open 2nd transistor

Test Data Document:

87990-755002a0670 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

4 ribbon all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0